

N-Channel Power MOSFET

600V, 13A, 0.26Ω

FEATURES

- Super-Junction technology
- High performance, small $R_{DS(ON)} * Q_g$ figure of merit (FOM)
- High ruggedness performance
- 100% UIS tested
- High commutation performance
- Pb-free plating
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS		
PARAMETER	VALUE	UNIT
V_{DS}	600	V
$R_{DS(on)}$ (max)	0.26	Ω
Q_g	30	nC



✓
RoHS
COMPLIANT

HALOGEN
FREE

APPLICATION

- Power Supply
- AC/DC LED Lighting



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current ^(Note 1)	I_D	13	A
		7.8	A
Pulsed Drain Current ^(Note 2)	I_{DM}	39	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	P_{DTOT}	32.1	W
Single Pulsed Avalanche Energy ^(Note 3)	E_{AS}	196.9	mJ
Single Pulsed Avalanche Current ^(Note 3)	I_{AS}	2.5	A
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to +150	°C

THERMAL PERFORMANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\Theta JC}$	3.9	°C/W
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	62	°C/W

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB with minimum recommended footprint in still air.

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static ^(Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}$, $I_D = 250\mu\text{A}$	BV_{DSS}	600	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	$V_{GS(\text{TH})}$	2.0	3.0	4.0	V
Gate Body Leakage	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$	I_{GSS}	--	--	± 100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600\text{V}$, $V_{GS} = 0\text{V}$	I_{DSS}	--	--	1	μA
Drain-Source On-State Resistance	$V_{GS} = 10\text{V}$, $I_D = 3.9\text{A}$	$R_{DS(\text{on})}$	--	0.19	0.26	Ω
Dynamic ^(Note 5)						
Total Gate Charge	$V_{DS} = 380\text{V}$, $I_D = 13\text{A}$, $V_{GS} = 10\text{V}$	Q_g	--	30	--	nC
Gate-Source Charge		Q_{gs}	--	6.6	--	
Gate-Drain Charge		Q_{gd}	--	11.7	--	
Input Capacitance	$V_{DS} = 100\text{V}$, $V_{GS} = 0\text{V}$, $f = 1.0\text{MHz}$	C_{iss}	--	1273	--	pF
Output Capacitance		C_{oss}	--	92	--	
Gate Resistance	$F = 1\text{MHz}$, open drain	R_g	--	3.1	--	Ω
Switching ^(Note 6)						
Turn-On Delay Time	$V_{DD} = 380\text{V}$, $R_{\text{GEN}} = 25\Omega$, $I_D = 13\text{A}$, $V_{GS} = 10\text{V}$,	$t_{d(on)}$	--	28.4	--	ns
Turn-On Rise Time		t_r	--	13.2	--	
Turn-Off Delay Time		$t_{d(off)}$	--	90.8	--	
Turn-Off Fall Time		t_f	--	10	--	
Source-Drain Diode ^(Note 4)						
Forward On Voltage	$I_S = 13\text{A}$, $V_{GS} = 0\text{V}$	V_{SD}	--	--	1.4	V
Reverse Recovery Time	$V_R = 100\text{V}$, $I_S = 13\text{A}$ $dI_F/dt = 100\text{A}/\mu\text{s}$	t_{rr}	--	346.6	--	ns
Reverse Recovery Charge		Q_{rr}	--	4.2	--	μC

Notes:

1. Current limited by package.
2. Pulse width limited by the maximum junction temperature.
3. $L = 63\text{mH}$, $I_{AS} = 2.5\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
4. Pulse test: $PW \leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
5. For DESIGN AID ONLY, not subject to production testing.
6. Switching time is essentially independent of operating temperature.

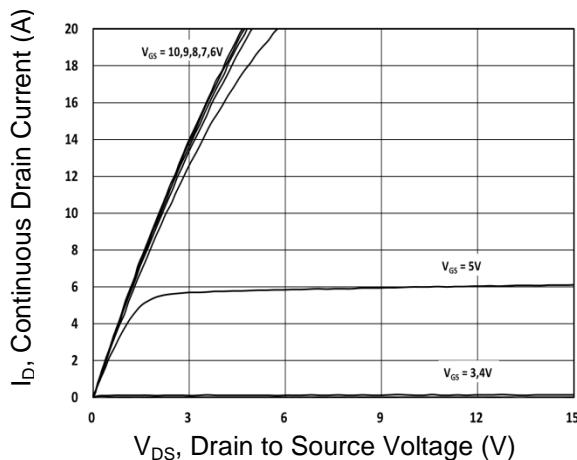
ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM60NB260CI C0G	ITO-220	50pcs / Tube

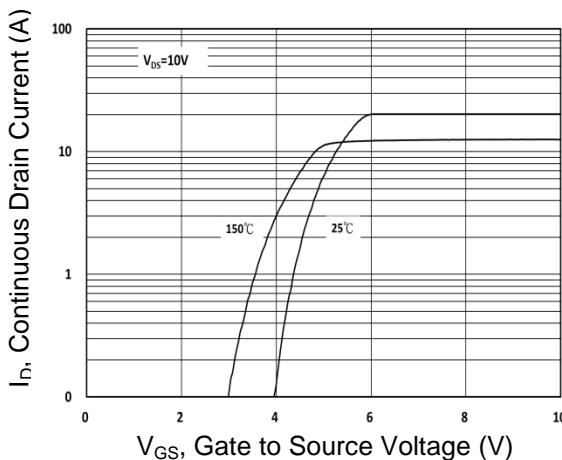
CHARACTERISTICS CURVES

($T_c = 25^\circ\text{C}$ unless otherwise noted)

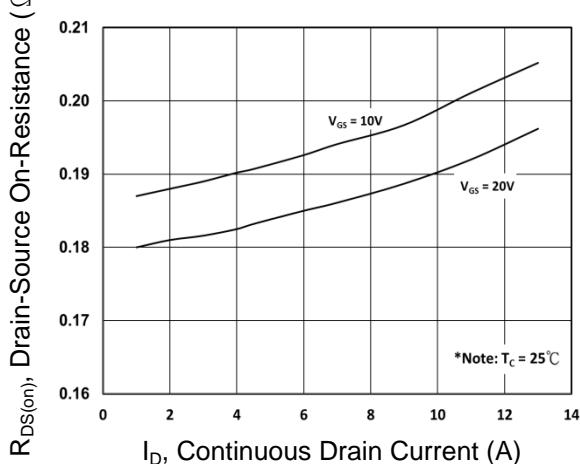
Output Characteristics



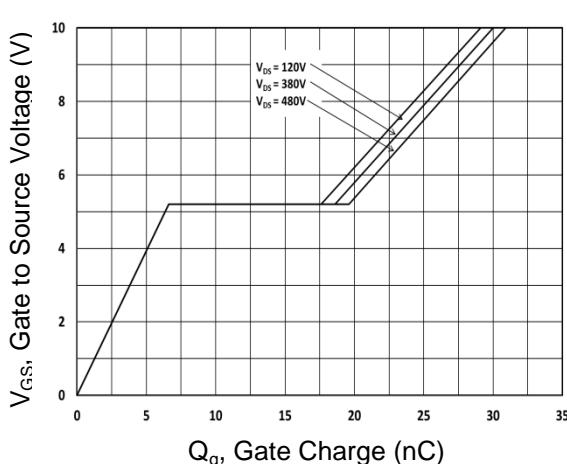
Transfer Characteristics



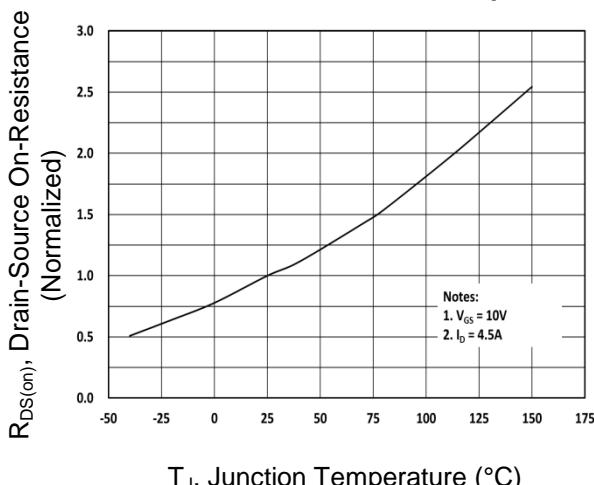
On-Resistance vs. Drain Current



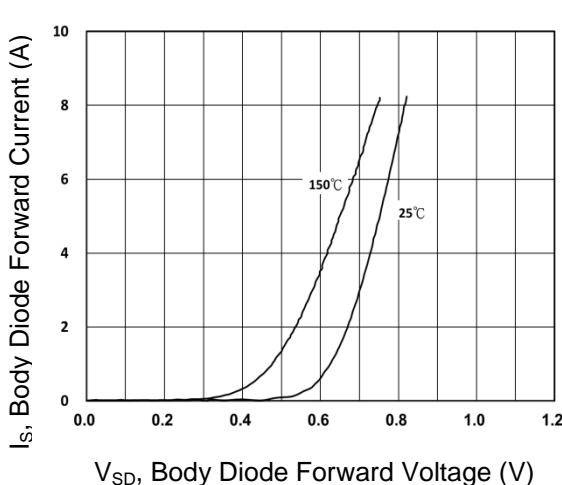
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



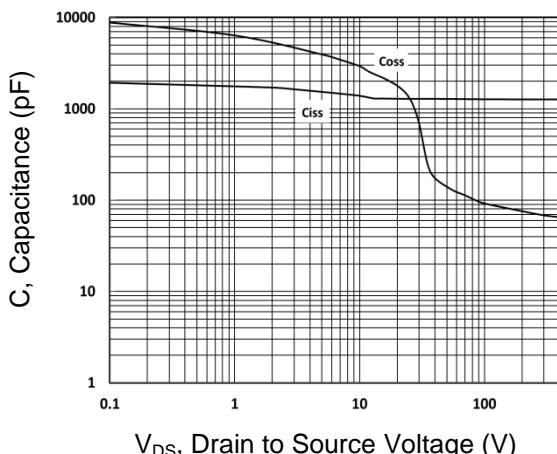
Source-Drain Diode Forward Current vs. Voltage



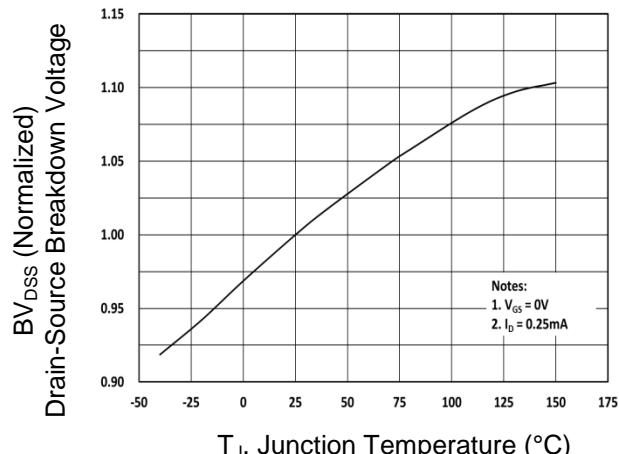
CHARACTERISTICS CURVES

($T_C = 25^\circ\text{C}$ unless otherwise noted)

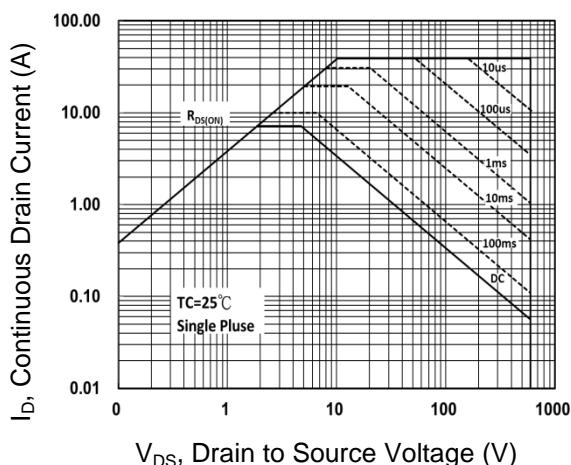
Capacitance vs. Drain-Source Voltage



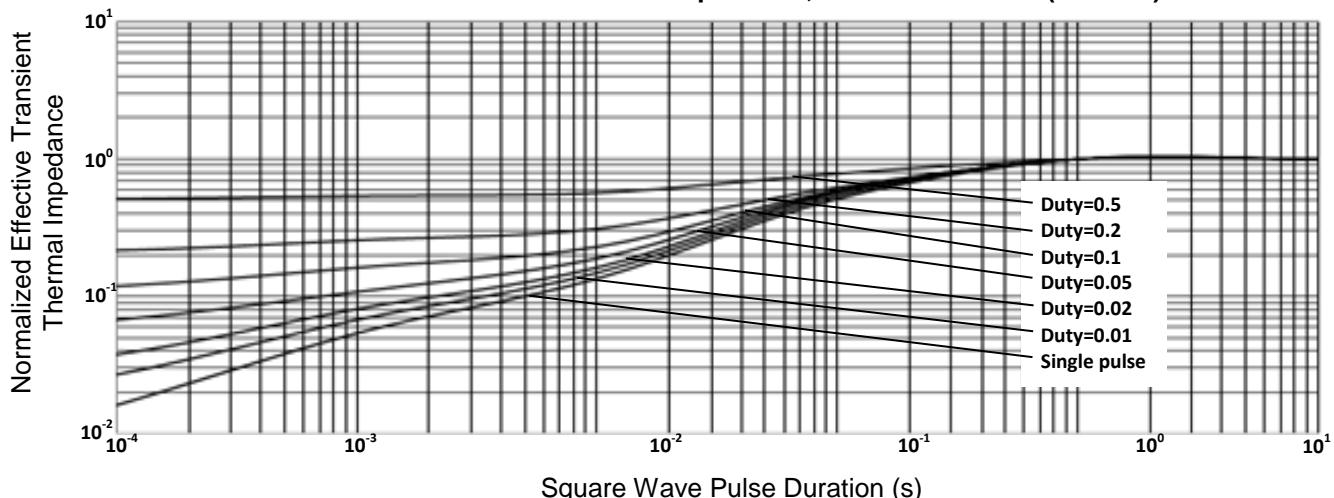
BV_{DSS} vs. Junction Temperature

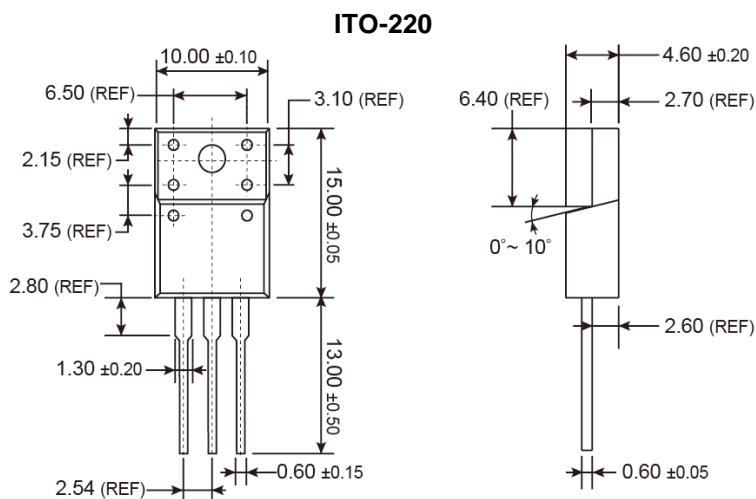


Maximum Safe Operating Area (ITO-220)



Normalized Thermal Transient Impedance, Junction-to-Case (ITO-220)



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

MARKING DIAGRAM


- G** = Halogen Free
- Y** = Year Code
- WW** = Week Code (01~52)
- F** = Factory Code

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- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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